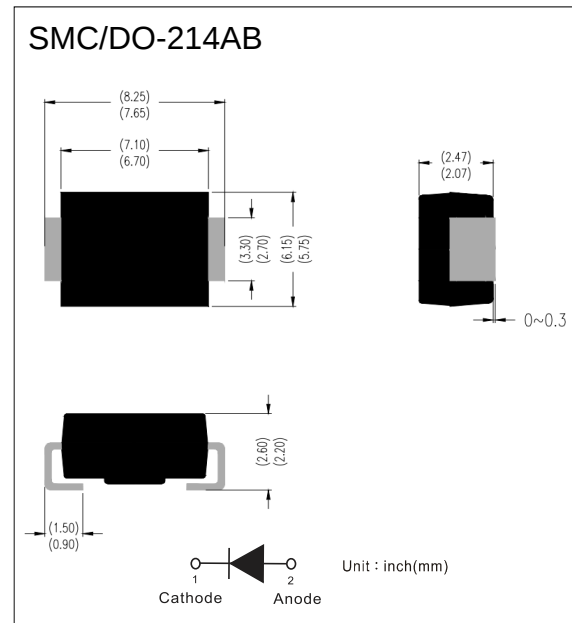


■ Features

- Glass passivated junction chip
- Ideal for automated placement
- Fast switching for high efficiency
- Comply with RoHS standard, halogen-free

■ Mechanical Data

- package: SMC/DO-214AB
- Polarity: Indicated by cathode band
- Epoxy: UL 94V-0 rate flame retardant
- Mounting Position : Any



■ Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	RS3A	RS3B	RS3D	RS3G	RS3J	RS3K	RS3M	UNIT
Repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Reverse voltage, total rms value	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Forward current	$I_{F(AV)}$	3							A
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	100							A
Junction temperature	T_J	- 55 to +150							$^{\circ}\text{C}$
Storage temperature	T_{STG}	- 55 to +150							$^{\circ}\text{C}$

■ Thermal Performance($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TYP	UNIT
Junction-to-lead thermal resistance per diode	$R_{\theta JL}$	15	$^{\circ}\text{C/W}$
Junction-to-ambient thermal resistance per diode	$R_{\theta JA}$	50	$^{\circ}\text{C/W}$

■ Electrical Specifications ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		CONDITIONS	SYMBOL	TYP.	MAX.	UNIT
Forward voltage per diode ⁽¹⁾		$I_F = 3\text{A}$, $T_J = 25^\circ\text{C}$	V_F	-	1.3	V
Reverse current @ rated V_R per diode ⁽²⁾		$T_J = 25^\circ\text{C}$	I_R	-	10	μA
		$T_J = 125^\circ\text{C}$		-	250	μA
Reverse recovery time	RS3A RS3B RS3D RS3G	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$ $I_{RR}=0.25\text{A}$	t_{rr}	-	150	ns
	RS3J			-	250	ns
	RS3K RS3M			-	500	ns

Notes:

1. Pulse test with $PW=0.3\text{ ms}$
2. Pulse test with $PW=30\text{ ms}$

■ Characteristics Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig.1 Forward Current Derating Curve

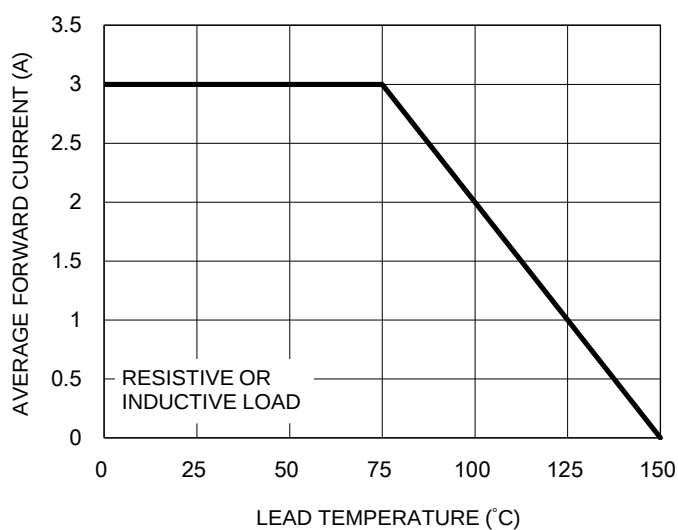


Fig.2 Typical Junction Capacitance

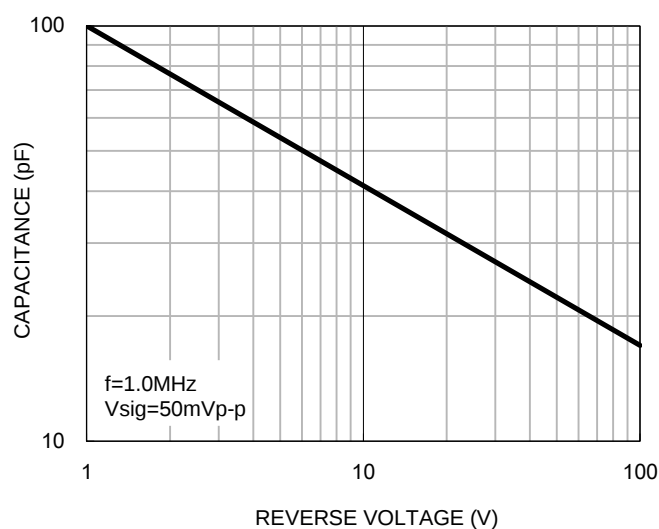




Fig.3 Typical Reverse Characteristics

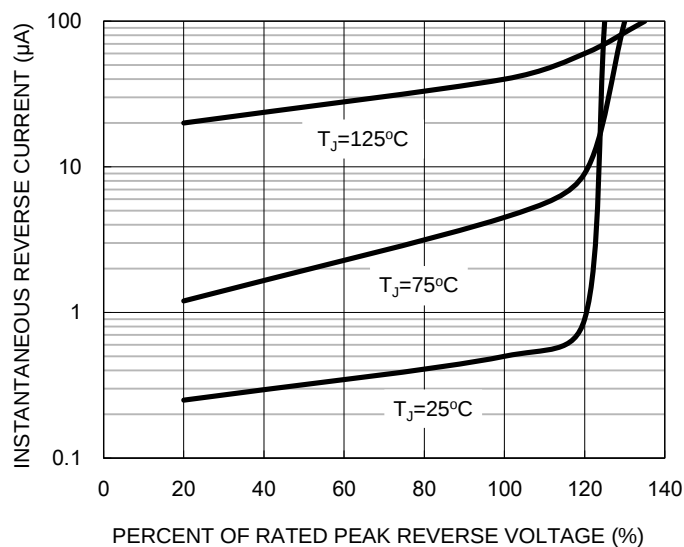


Fig.4 Typical Forward Characteristics

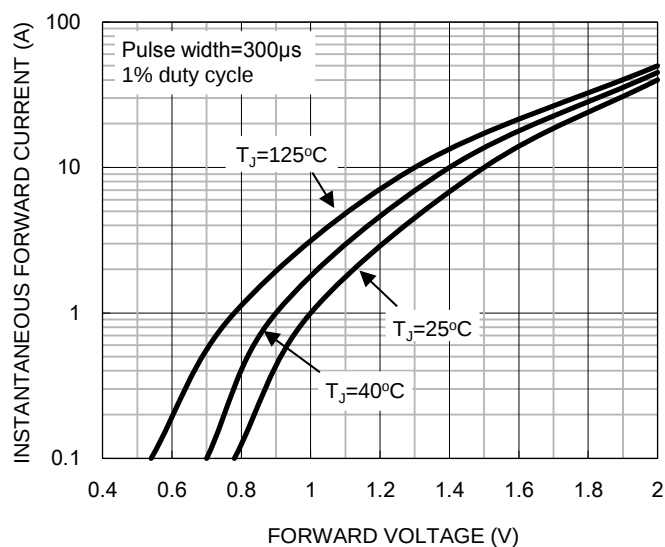


Fig.5 Maximum Non-repetitive Forward Surge Current

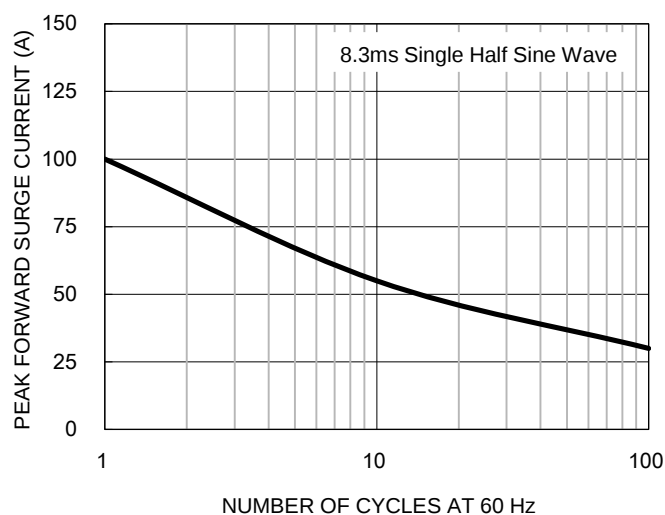


Fig.6 Reverse Recovery Time Characteristic And Test Circuit Diagram

